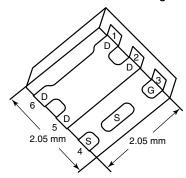




P-Channel 20 V (D-S) MOSFET

PRODUCT SUMMARY									
V _{DS} (V)	$R_{DS(on)}$ (Ω) Max.	I _D (A)	Q _g (Typ.)						
- 20	$0.0165 \text{ at V}_{GS} = -4.5 \text{ V}$	- 12 ^a							
	$0.0185 \text{ at V}_{GS} = -3.7 \text{ V}$	- 12 ^a	23 nC						
	0.0300 at V _{GS} = - 2.5 V	- 12 ^a							

PowerPAK SC-70-6L-Single



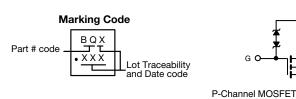
Ordering Information: SiA445EDJ-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

- Halogen-free According to IEC 61249-2-21 **Definition**
- TrenchFET® Power MOSFET
- Thermally Enhanced PowerPAK® SC-70 Package
 - Small Footprint Area
 - Low On-Resistance
- 100 % $\rm R_{\rm g}$ Tested Built in ESD Protection with Zener Diode
- Typical ESD Performance: 2000 V
- Compliant to RoHS Directive 2002/95/EC

APPLICATIONS

- Smart Phones, Tablet PCs, Mobile Computing
 - Battery Switch
 - Charger Switch
 - Load Switch





HALOGEN FREE

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)								
Parameter		Symbol	Limit	Unit				
Drain-Source Voltage		V_{DS}	- 20	V				
Gate-Source Voltage		V_{GS}	± 12	7				
	T _C = 25 °C		- 12 ^a					
Continuous Drain Current (T _{.I} = 150 °C)	T _C = 70 °C	ı_	- 12 ^a	1				
Continuous Dialit Current (1) = 150 C)	T _A = 25 °C	I _D	- 11.8 ^{b, c}	1				
	T _A = 70 °C		- 9.5 ^{b, c}	Α				
Pulsed Drain Current (t = 300 μs)		I _{DM}	- 50	1				
Continuous Source-Drain Diode Current	$T_C = 25 ^{\circ}C$	Is	- 12 ^a					
Continuous Cource Diam Blode Current	T _A = 25 °C	'S	- 2.9 ^{b, c}					
	T _C = 25 °C		19					
Maximum Power Dissipation	T _C = 70 °C	P _D	12	w				
Maximum i ower bissipation	T _A = 25 °C	' D	3.5 ^{b, c}	7 **				
	T _A = 70 °C		2.2 ^{b, c}					
Operating Junction and Storage Temperature Range	je	T _J , T _{stg}	- 55 to 150	- °C				
Soldering Recommendations (Peak Temperature) ^d	, e		260]				

THERMAL RESISTANCE RATINGS									
Parameter		Symbol	Typical	Maximum	Unit				
Maximum Junction-to-Ambient ^{b, f}	t ≤ 5 s	R _{thJA}	28	36	°C/W				
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	5.3	6.5	J/VV				

Notes:

- a. Package limited.
- b. Surface mounted on 1" x 1" FR4 board.
- d. See solder profile (www.vishay.com/doc?73257). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
- f. Maximum under steady state conditions is 80 °C/W.

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SiA445EDJ

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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit			
Static									
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$	- 20			V			
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$			- 13					
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	I _D = - 250 μA		2.6		mV/°C			
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = - 250 μA	- 0.5		- 1.2	V			
-	_	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$			± 60	μΑ			
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 4.5 \text{ V}$			± 1				
		V _{DS} = - 20 V, V _{GS} = 0 V			- 1				
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 20 V, V _{GS} = 0 V, T _J = 55 °C			- 10				
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	- 20			Α			
	. ,	V _{GS} = - 4.5 V, I _D = - 7 A		0.0135	0.0165	Ω			
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 3.7 V, I _D = - 5 A		0.0150	0.0185				
	, ,	V _{GS} = - 2.5 V, I _D = - 5 A		0.0210	0.0300	†			
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 10 V, I _D = - 7 A		29		S			
Dynamic ^b									
Input Capacitance	C _{iss}			2130		pF			
Output Capacitance	C _{oss}	V _{DS} = - 10 V, V _{GS} = 0 V, f = 1 MHz		290					
Reverse Transfer Capacitance	C _{rss}	20 40		280					
Total Gate Charge		V _{DS} = - 10 V, V _{GS} = - 10 V, I _D = - 12 A		48	72	nC			
	Q_g	30 30 2		23	35				
Gate-Source Charge	Q _{gs}	$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -12 \text{ A}$		3.1					
Gate-Drain Charge	Q _{gd}			6.7					
Gate Resistance	R _g	f = 1 MHz	1.2	6	12	Ω			
Turn-On Delay Time	t _{d(on)}			25	50				
Rise Time	t _r	V_{DD} = - 10 V, R_L = 1 Ω		25	50				
Turn-Off Delay Time	t _{d(off)}	$I_D\cong$ - 9.5 A, V_{GEN} = - 4.5 V, R_g = 1 Ω		55	110				
Fall Time	t _f			20	40				
Turn-On Delay Time	t _{d(on)}			7	15	ns			
Rise Time	t _r	V_{DD} = - 10 V, R_L = 1 Ω		10	20				
Turn-Off Delay Time	t _{d(off)}	$I_D\cong$ - 9.5 A, $V_{GEN}=$ - 10 V, $R_g=$ 1 Ω		60	120				
Fall Time	t _f			17	35				
Drain-Source Body Diode Characterist	ics			•					
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			- 12	А			
Pulse Diode Forward Current I _{SM}					- 50	_ ^			
Body Diode Voltage	V_{SD}	I _S = - 9.5 A, V _{GS} = 0 V		- 0.8	- 1.2	V			
Body Diode Reverse Recovery Time	t _{rr}			15	30	ns			
Body Diode Reverse Recovery Charge	Q _{rr}	$I_F = -9.5 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s},$		5	10	nC			
Reverse Recovery Fall Time	t _a	T _J = 25 °C		7		ns			
Reverse Recovery Rise Time	t _b			8					

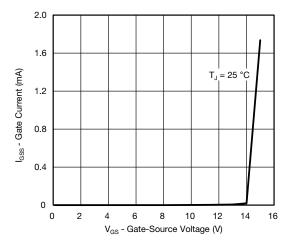
Notes:

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

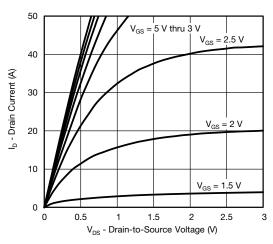
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



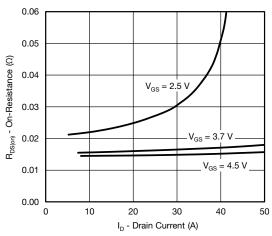
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



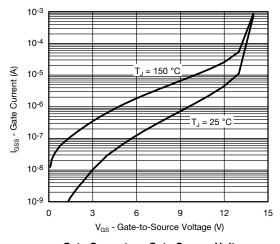
Gate Current vs. Gate-Source Voltage



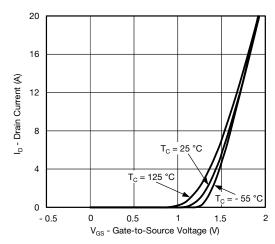
Output Characteristics



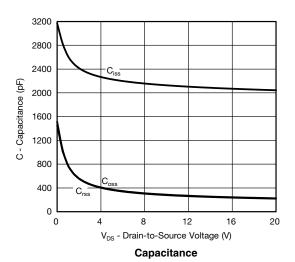
On-Resistance vs. Drain Current



Gate Current vs. Gate-Source Voltage



Transfer Characteristics

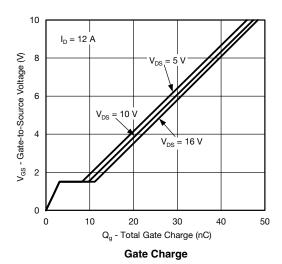


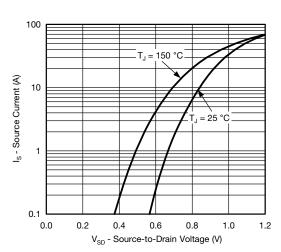
SiA445EDJ

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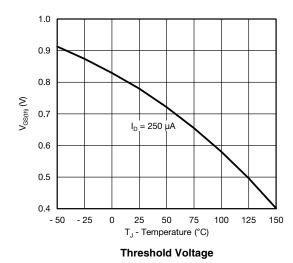
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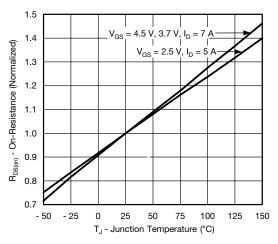
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



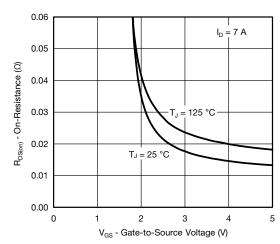




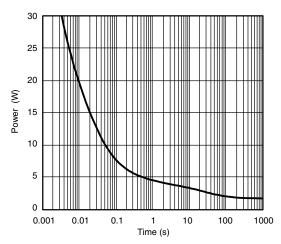




On-Resistance vs. Junction Temperature



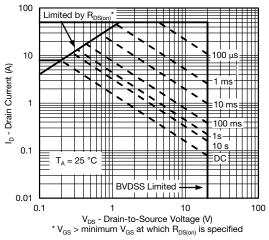
On-Resistance vs. Gate-to-Source Voltage



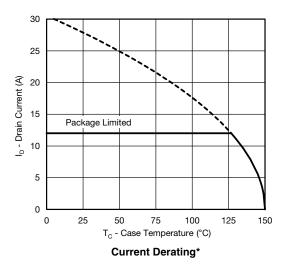
Single Pulse Power, Junction-to-Ambient

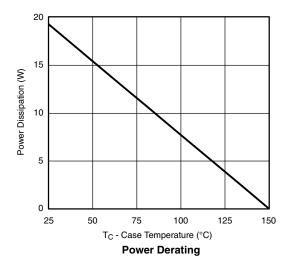


TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Safe Operating Area, Junction-to-Ambient





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^{*} The power dissipation PD is based on TJ(max) = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

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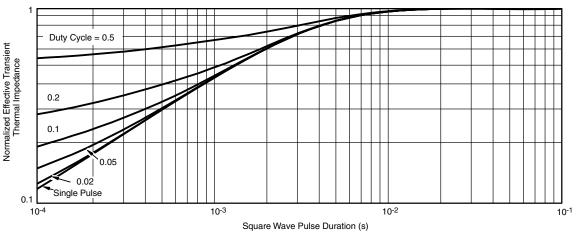
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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



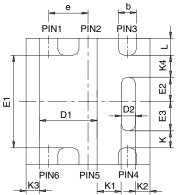
Normalized Thermal Transient Impedance, Junction-to-Case

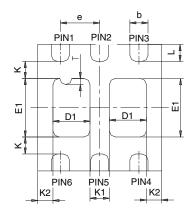
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppq?63619.





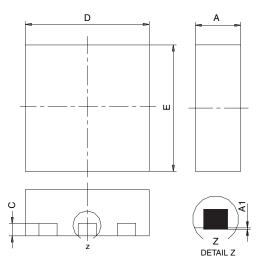
PowerPAK® SC70-6L





BACKSIDE VIEW OF SINGLE

BACKSIDE VIEW OF DUAL



- All dimensions are in millimeters
 Package outline exclusive of mold flash and metal burr
 Package outline inclusive of plating

	SINGLE PAD						DUAL PAD					
DIM	MILLIMETERS			INCHES			MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max
Α	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002
b	0.23	0.30	0.38	0.009	0.012	0.015	0.23	0.30	0.38	0.009	0.012	0.015
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010
D	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
D1	0.85	0.95	1.05	0.033	0.037	0.041	0.513	0.613	0.713	0.020	0.024	0.028
D2	0.135	0.235	0.335	0.005	0.009	0.013						
E	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
E1	1.40	1.50	1.60	0.055	0.059	0.063	0.85	0.95	1.05	0.033	0.037	0.041
E2	0.345	0.395	0.445	0.014	0.016	0.018						
E3	0.425	0.475	0.525	0.017	0.019	0.021						
е		0.65 BSC			0.026 BSC	;	0.65 BSC			0.026 BSC		
K		0.275 TYP 0.011 TYP		0.275 TYP			0.011 TYP					
K1		0.400 TYP	400 TYP 0.016 TYP		0.320 TYP			0.013 TYP				
K2		0.240 TYP 0.009 TYP		0.252 TYP			0.010 TYP					
К3		0.225 TYP 0.009 TYP				•		•	•			
K4		0.355 TYP		0.014 TYP								
L	0.175	0.275	0.375	0.007	0.011	0.015	0.175	0.275	0.375	0.007	0.011	0.015
T							0.05	0.10	0.15	0.002	0.004	0.006

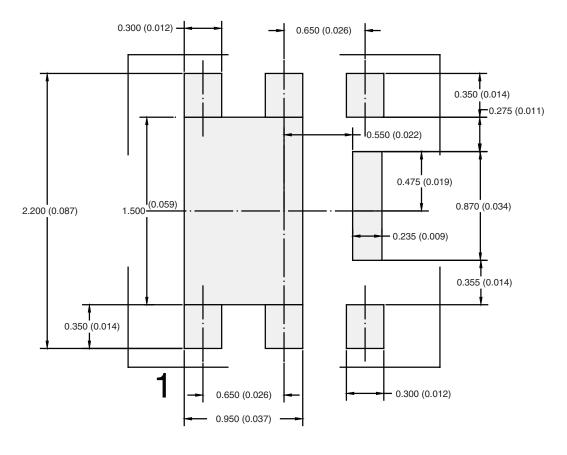
ECN: C-07431 - Rev. C, 06-Aug-07

DWG: 5934

06-Aug-07



RECOMMENDED PAD LAYOUT FOR PowerPAK® SC70-6L Single



Dimensions in mm/(Inches)

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ATTLICATION NOT



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Revision: 02-Oct-12 Document Number: 91000